

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~striketrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please AMEND claims **1, 3 and 5** and CANCEL claim **2** in accordance with the following:

Listing of the Claims

1. (Currently Amended) A thin film forming method for plasmatizing a mixture gas, the mixture gas consisting of a monomer gas and an oxidizing reactive gas, and for forming a thin film on a surface of a substrate, the thin film being made of an oxide, the method comprising:

~~a first step of forming~~ a first thin film by plasmatizing the mixture gas while varying a supply flow amount ratio of the monomer gas with respect to the reactive gas; and

~~a second step of forming~~ a final thin film by increasing the supply flow amount ratio after the forming of the first film-forming step, wherein:

~~the first step of forming~~ of the first thin film is performed under a first condition that the supply flow amount ratio decreases continuously from an initial value into a specific value of is 0.05 or lower within 2 to 5 seconds, and the flow amount of monomer gas is gradually reduced while the amount of the oxidizing reactive gas is maintained at a substantially fixed level; and

~~the second step of forming~~ of the final thin film is performed under a second condition that the supply flow amount ratio of monomer gas with respect to the reactive gas reaches 1000 or more, and ~~the second step of forming~~ of the final thin film lasts for 1 to 3 seconds.

2. (Cancelled)

3. (Currently Amended) The A- thin film forming method according to claim 12, wherein an initial value of the supply flow amount ratio in the forming of the first thin film forming

4. (Cancelled).

5. (Currently Amended) The A- thin film forming method according to claim 1, ~~2~~ or 3, wherein the mixture gas is plasmatized by controlling reflected power to be 10% or lower than supplied high frequency power, the reflected power being generated by supplying high frequency power of 100 MHz or lower to a high frequency electrode through an impedance matching network.

6-17. (Cancelled).

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